

1/16

FIG. 1(A)

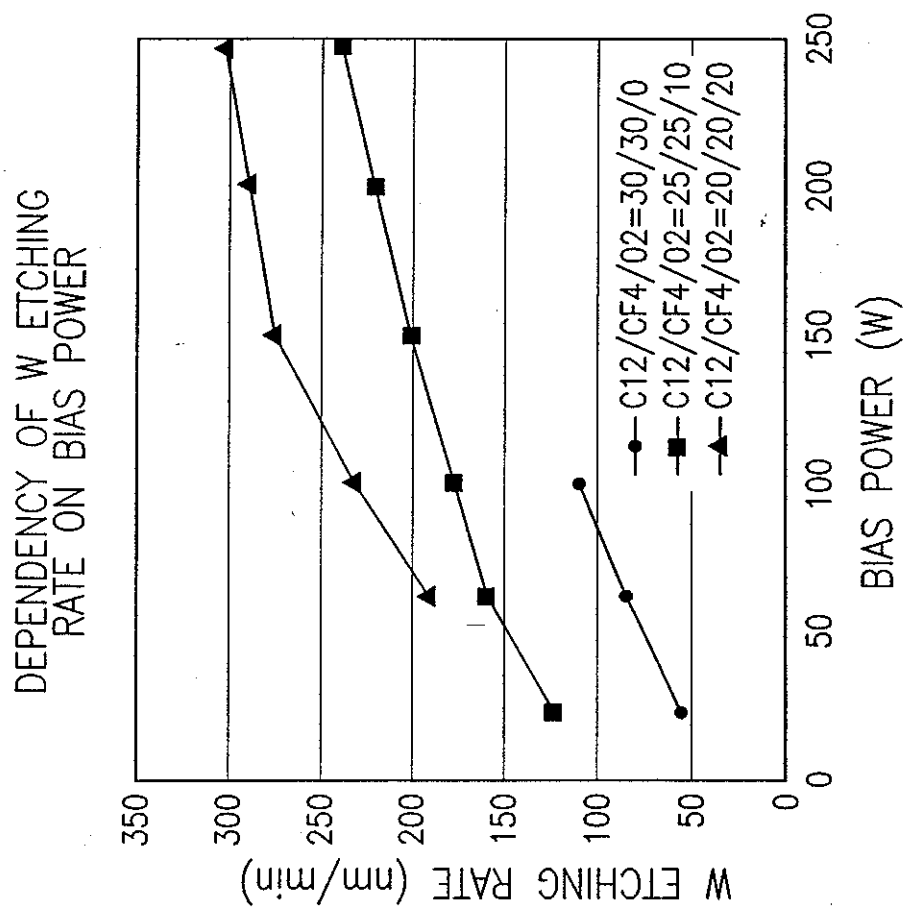
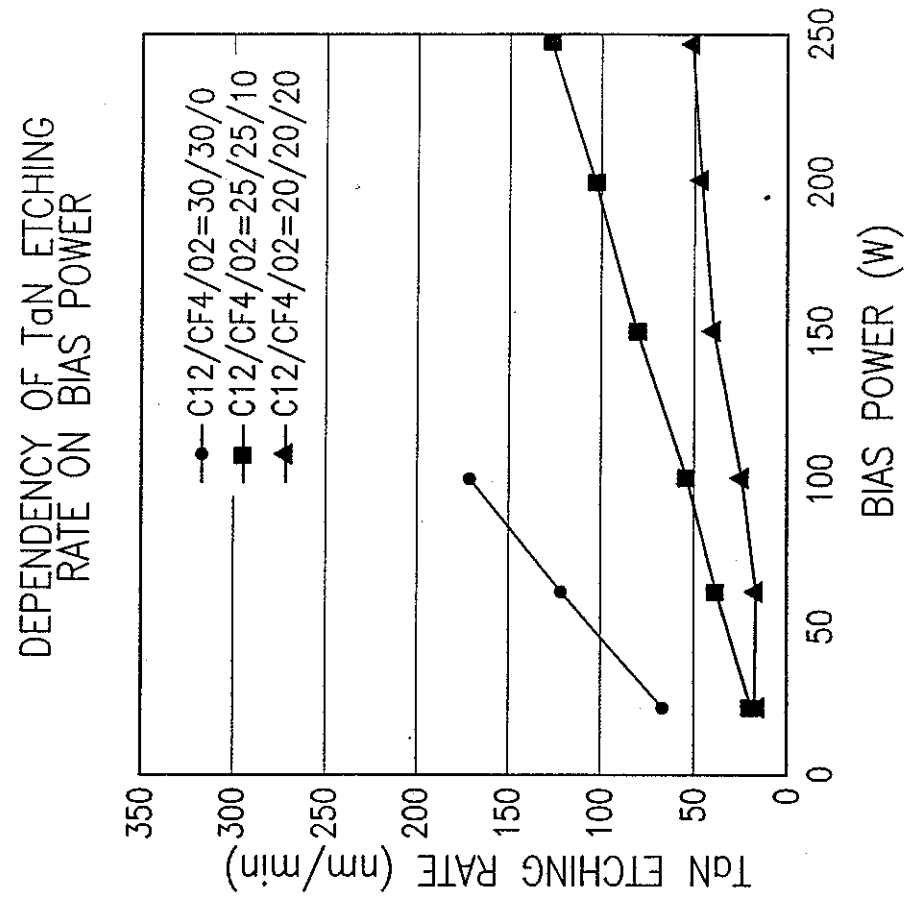


FIG. 1(B)



2/16

FIG. 1(C)

DEPENDENCY OF SELECTION RATIO
OF W AND TaN ON BIAS POWER
AND GAS FLOW

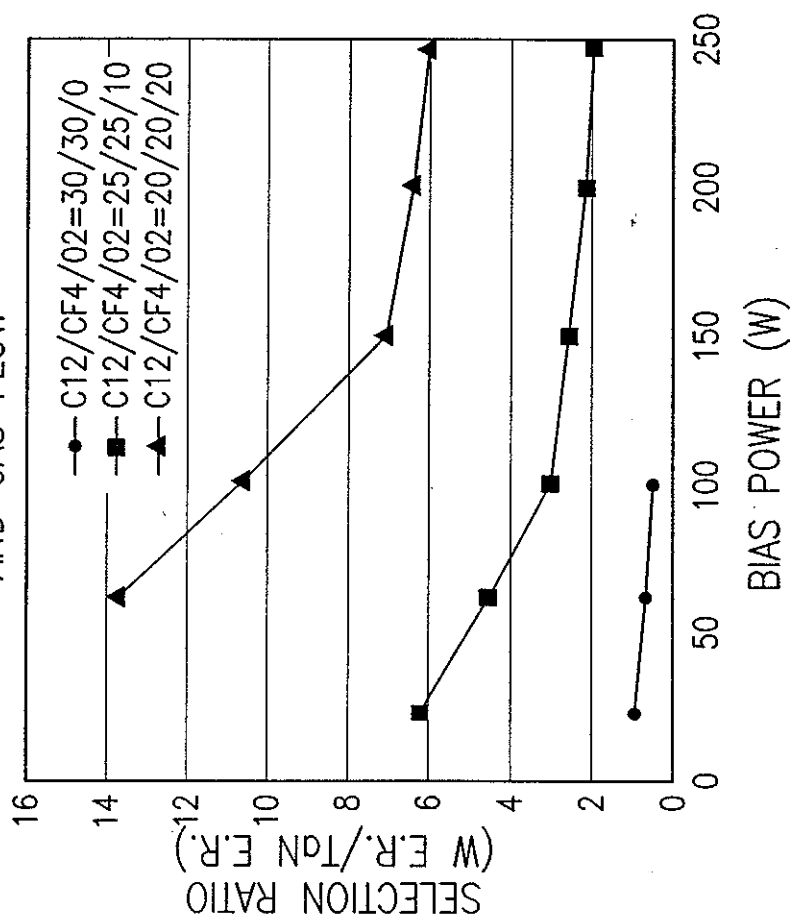
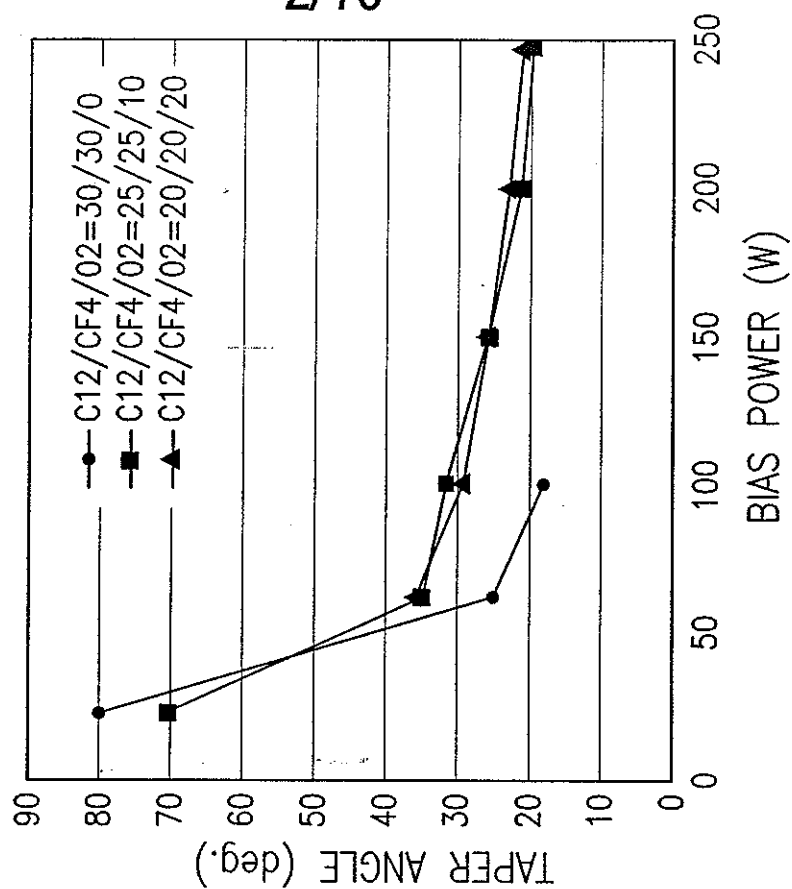


FIG. 1(D)

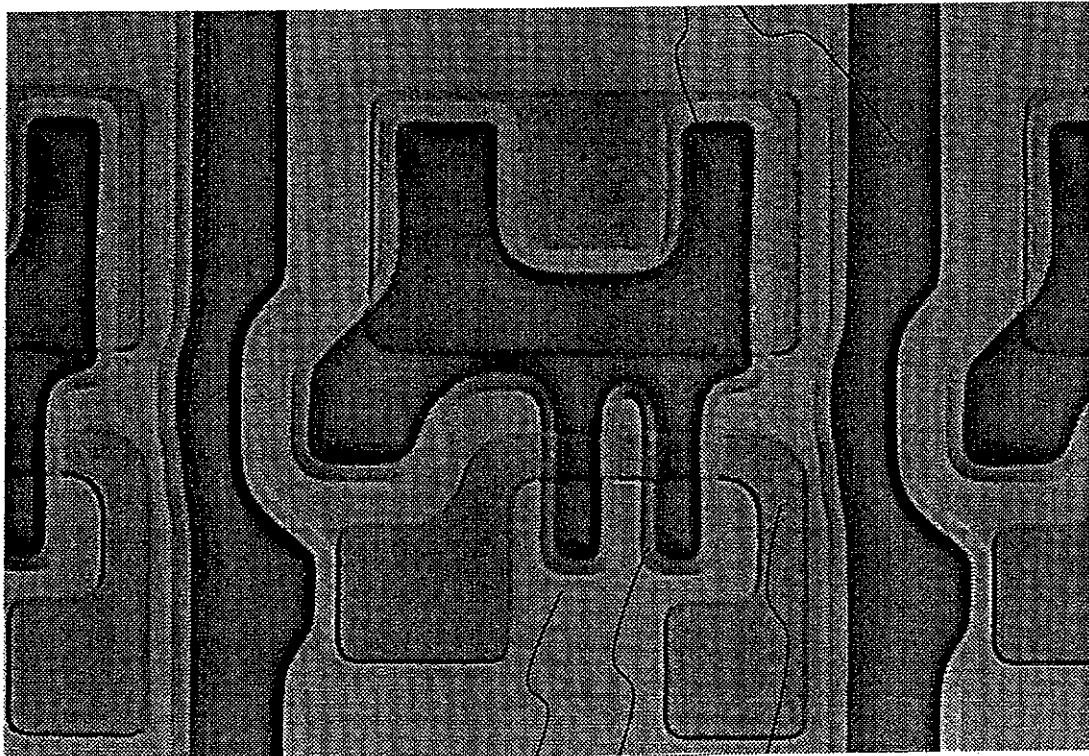
DEPENDENCY OF W TAPER
ANGLE ON BIAS POWER



3/16

FIG. 2(A)

(CONDITION 7): ICP POWER OF 500W, BIAS POWER OF 150W,
CHAMBER PRESSURE OF 1.0Pa, $\text{Cl}_2=25\text{sccm}$,
 $\text{CF}_4=25\text{sccm}$, $\text{O}_2=10\text{sccm}$

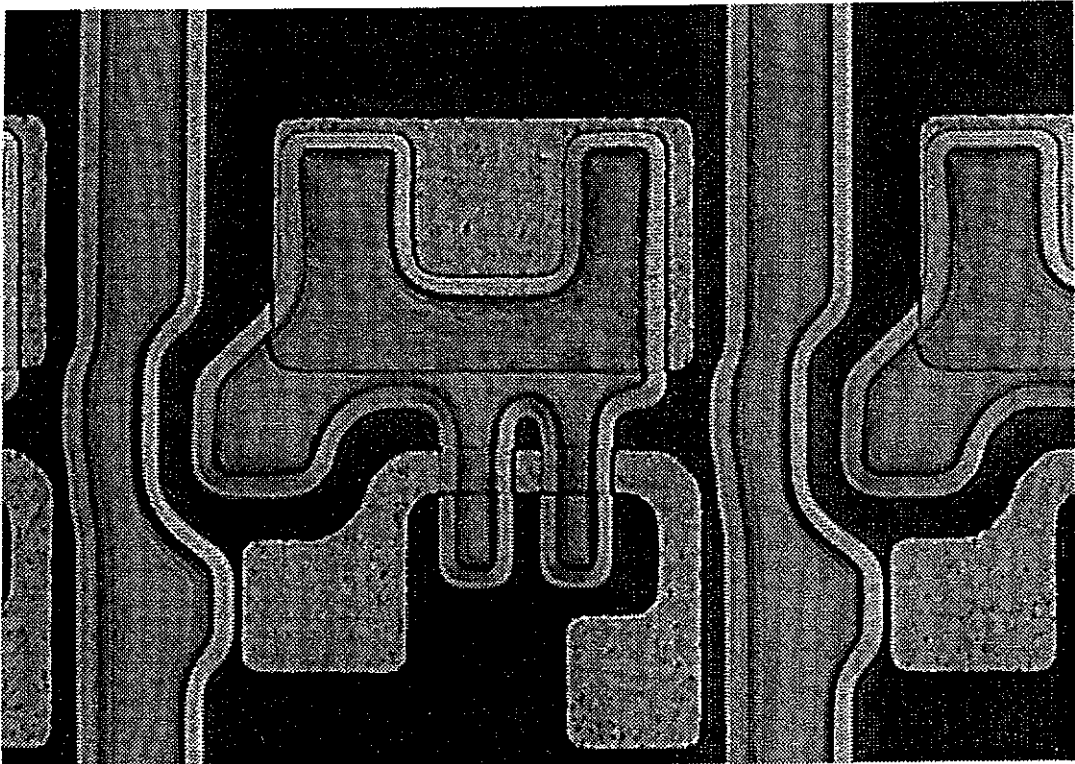


4/16

FIG. 2(B)

AFTER ETCHING TREATMENT UNDER CONDITION 7

(CONDITION 1): ICP POWER OF 500W, BIAS POWER OF 20W,
CHAMBER PRESSURE OF 1.0Pa,
 $\text{Cl}_2=30\text{sccm}$, $\text{CF}_4=30\text{sccm}$



5/16

FIG. 3(A)

FIRST DRY ETCHING

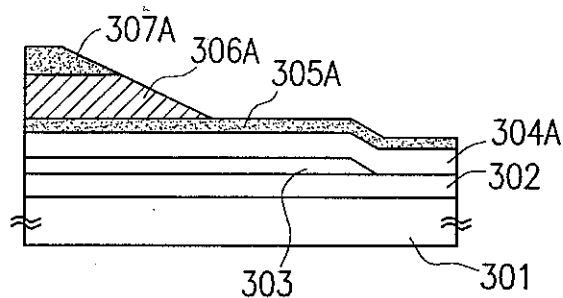


FIG. 3(B)

SECOND DRY ETCHING
DOPING

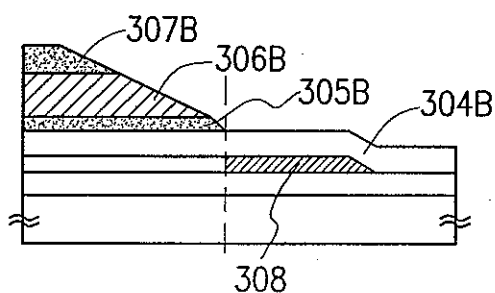


FIG. 3(C)

THIRD DRY ETCHING

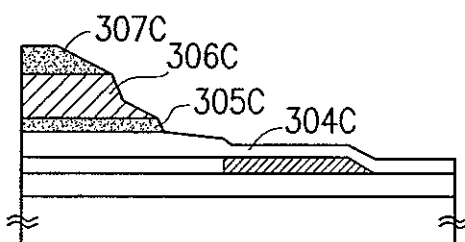


FIG. 3(D)

FOURTH DRY ETCHING

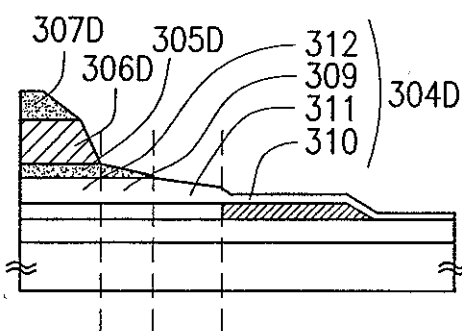
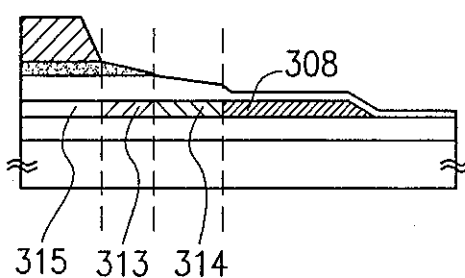


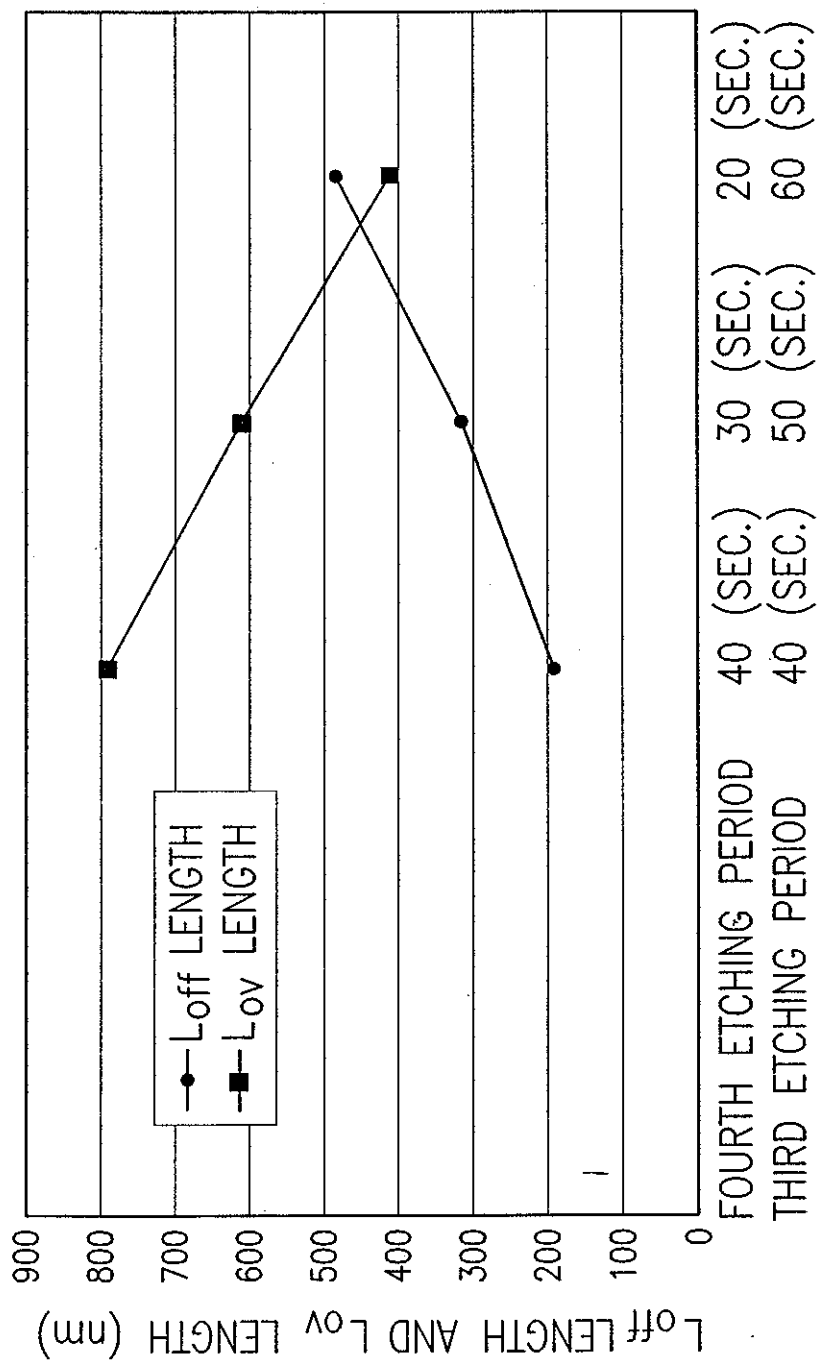
FIG. 3(E)

PEELING OF RESIST
DOPING



6/16

FIG. 4



VARIATION OF L_{off} LENGTH AND L_{ov} LENGTH
CHANGE OF ETCHING PERIOD

7/16

FIG. 5(A) FORMATION OF SEMICONDUCTOR LAYER/FORMATION OF INSULATING FILM/FORMATION OF FIRST CONDUCTING FILM AND SECOND CONDUCTING FILM/MASK FORMATION

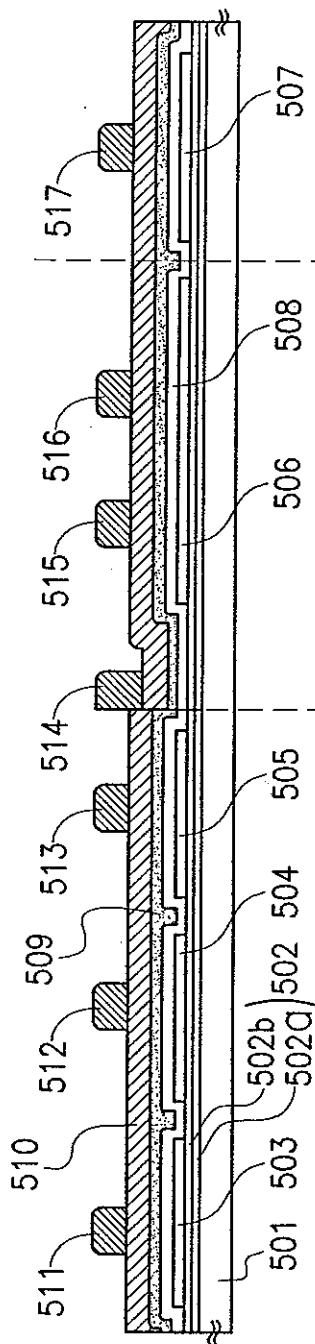


FIG. 5(B) FIRST ETCHING AND SECOND ETCHING/SECOND DOPING

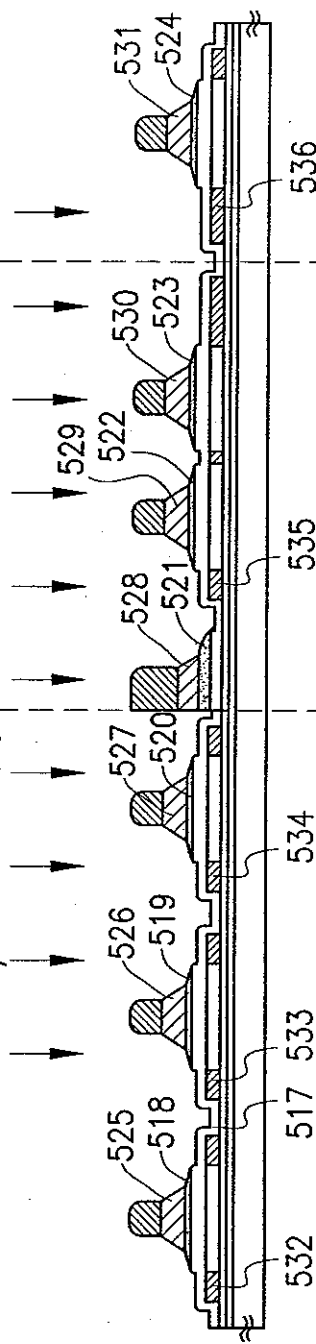
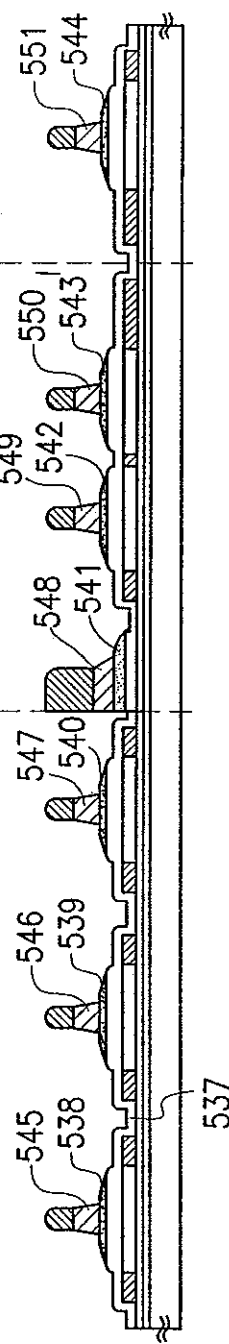


FIG. 5(C) THIRD ETCHING AND FOURTH ETCHING



8/16

FIG. 6(A) THIRD DOPING

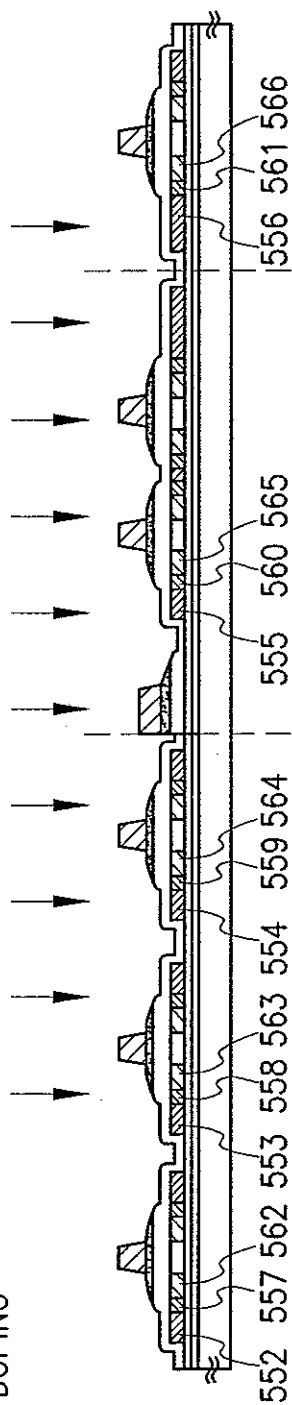


FIG. 6(B) FOURTH DOPING

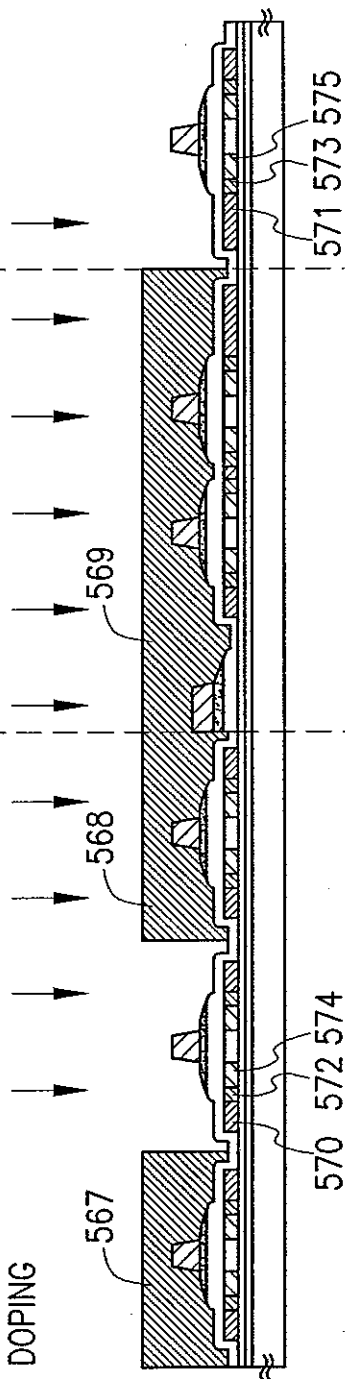
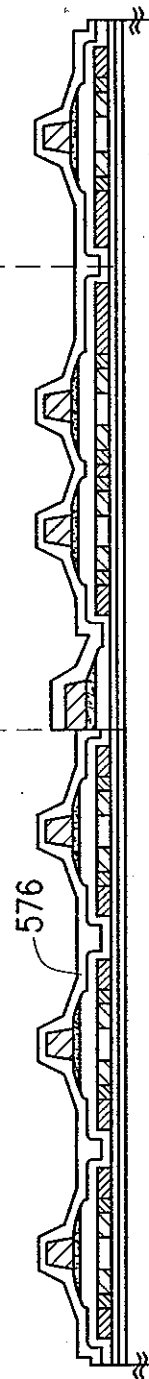
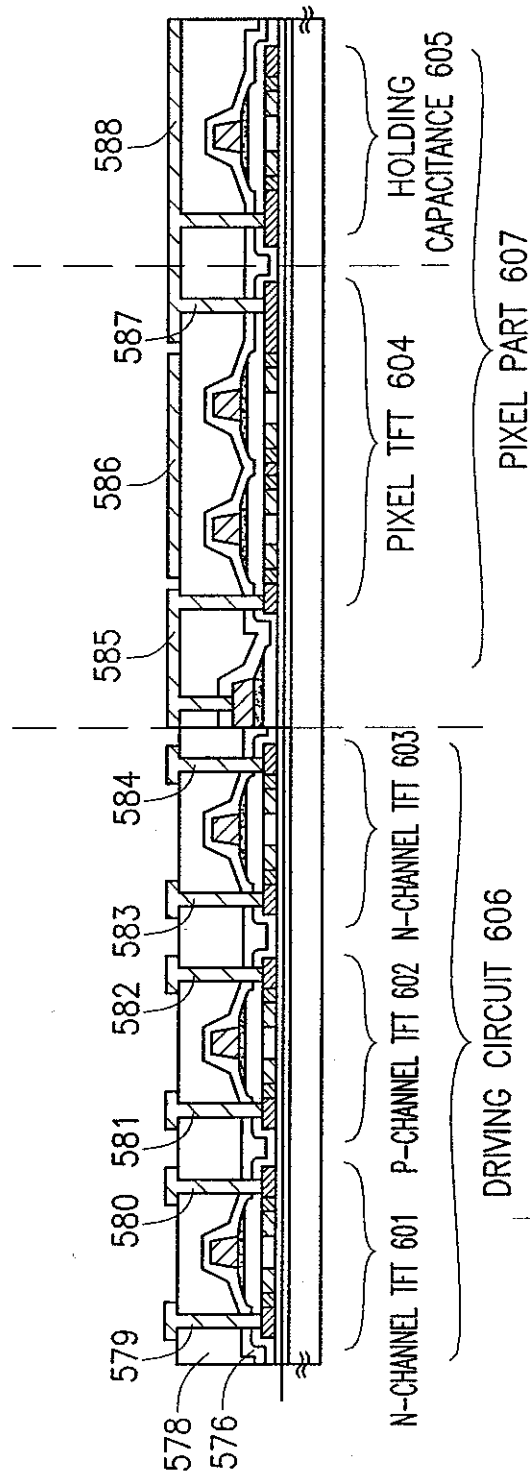


FIG. 6(C) ACTIVATION STEP



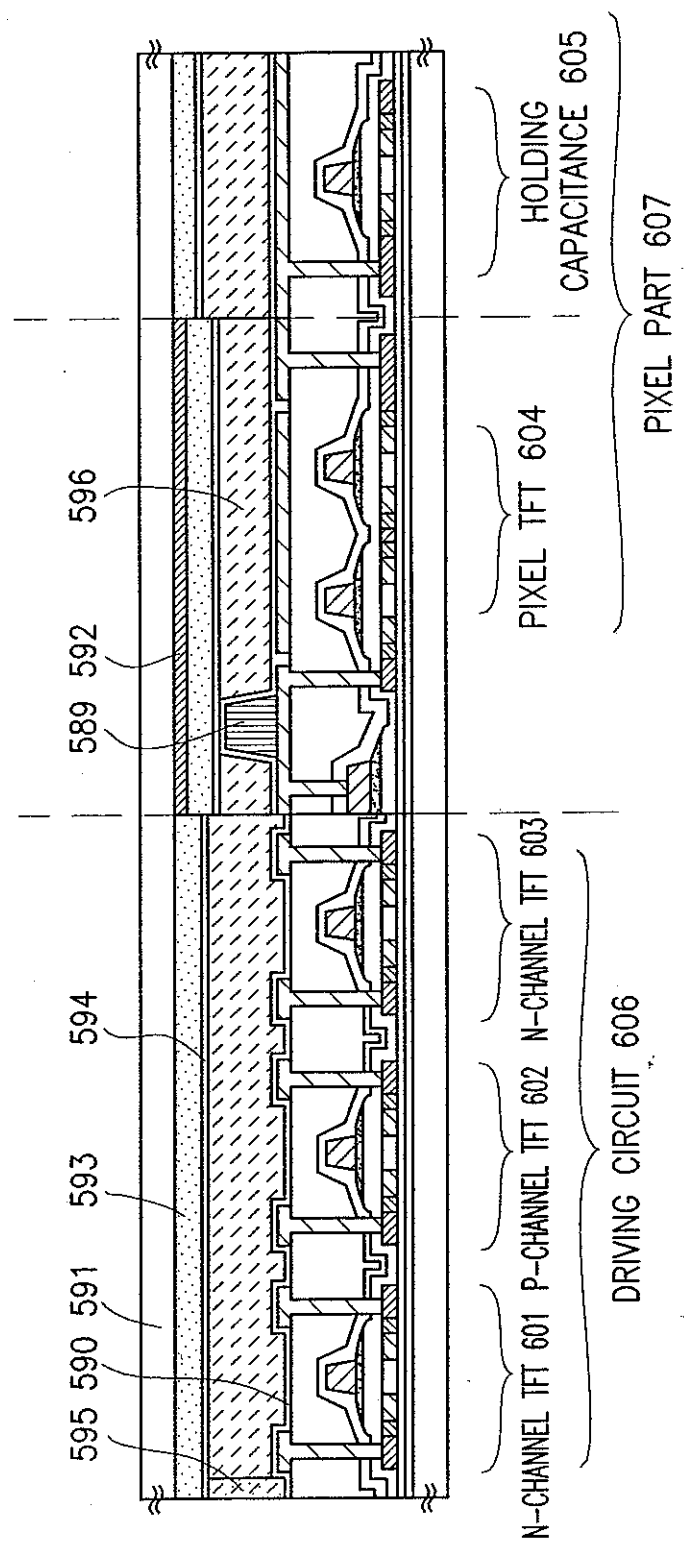
9/16

FIG. 7



10/16

FIG. 8



11/16

FIG. 9(A)
FIRST DRY ETCHING

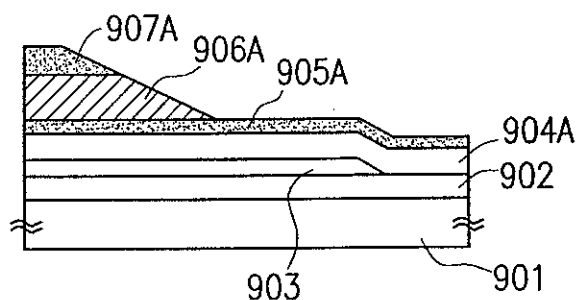


FIG. 9(B)
SECOND DRY ETCHING
DOPING

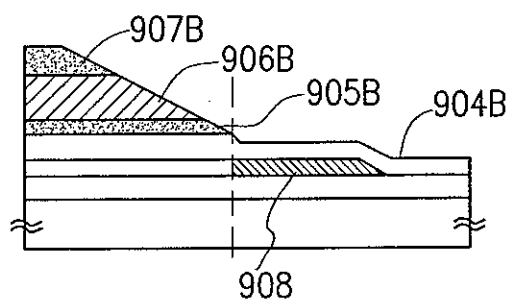


FIG. 9(C)
THIRD DRY ETCHING
DOPING

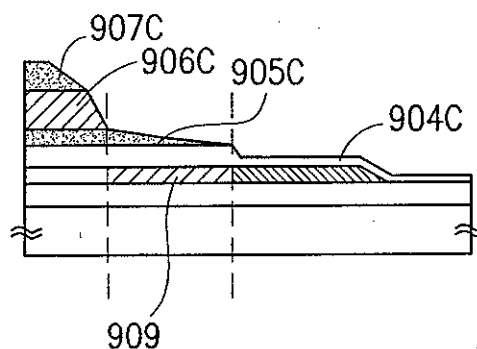


FIG. 9(D)
FOURTH DRY ETCHING

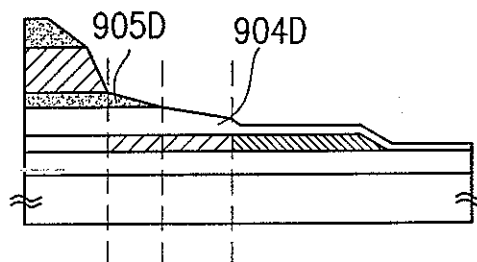
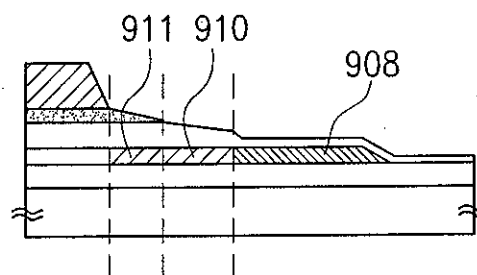


FIG. 9(E)
PEELING OF RESIST



12/16

FIG. 10(A)

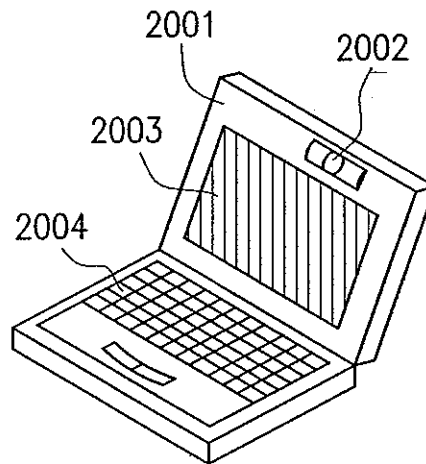


FIG. 10(B)

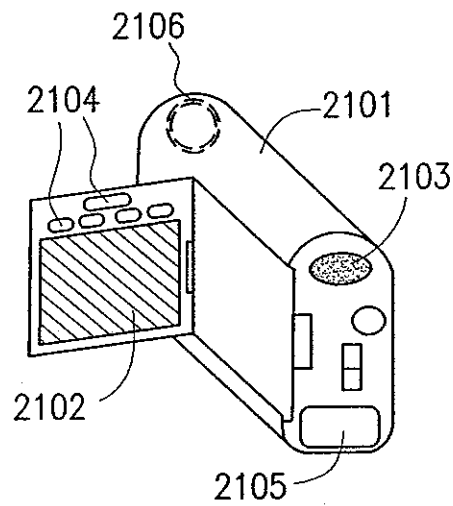
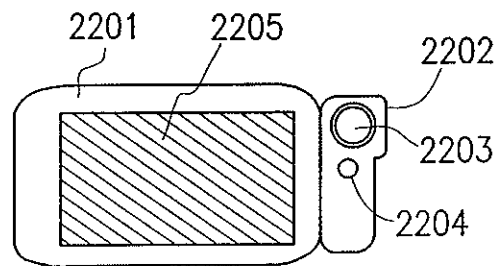


FIG. 10(C)



13/16

FIG. 10(D)

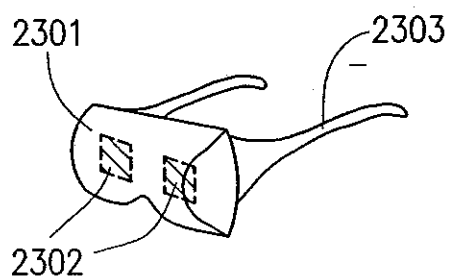


FIG. 10(E)

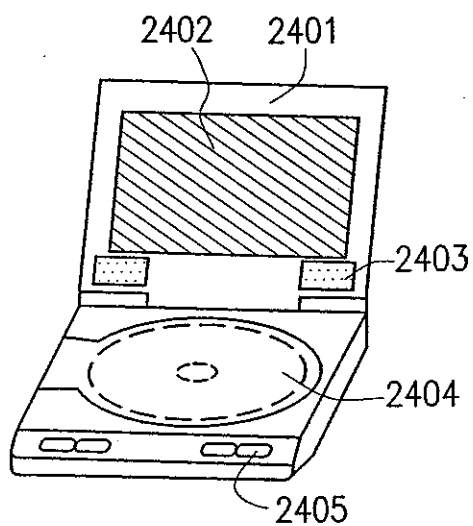
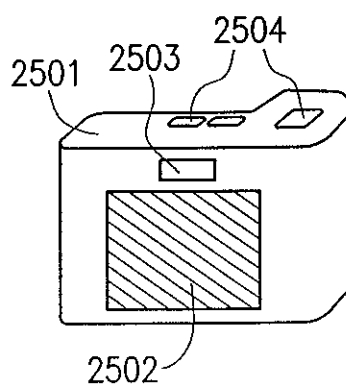


FIG. 10(F)



14/16

FIG. 11(A)

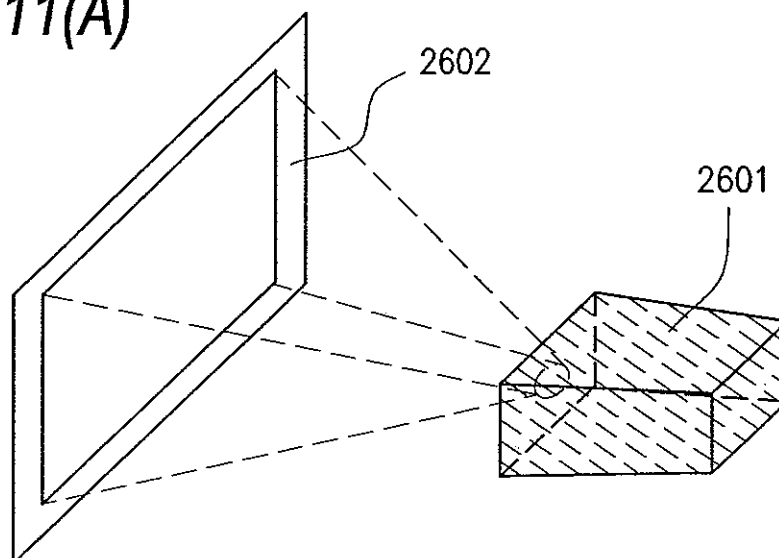
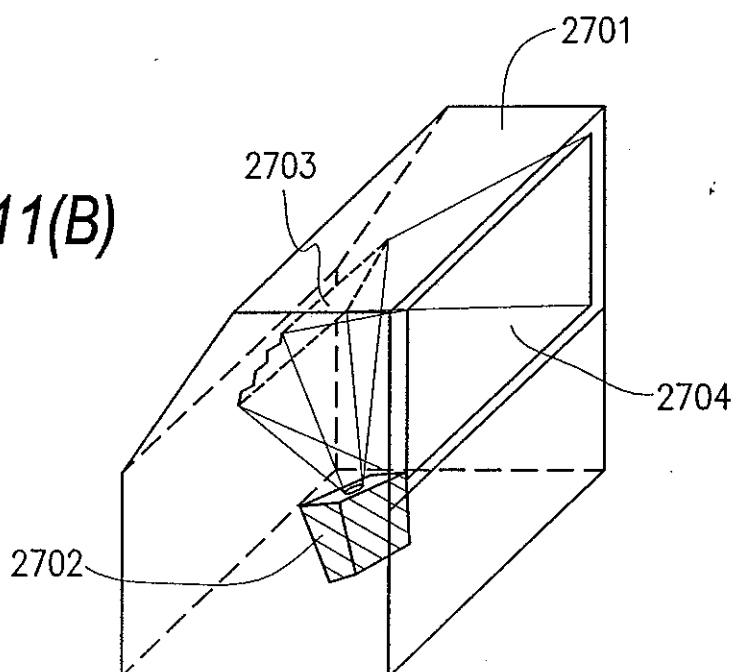


FIG. 11(B)



15/16

FIG. 11(C) PROJECTION DEVICE (3-PLATE TYPE)

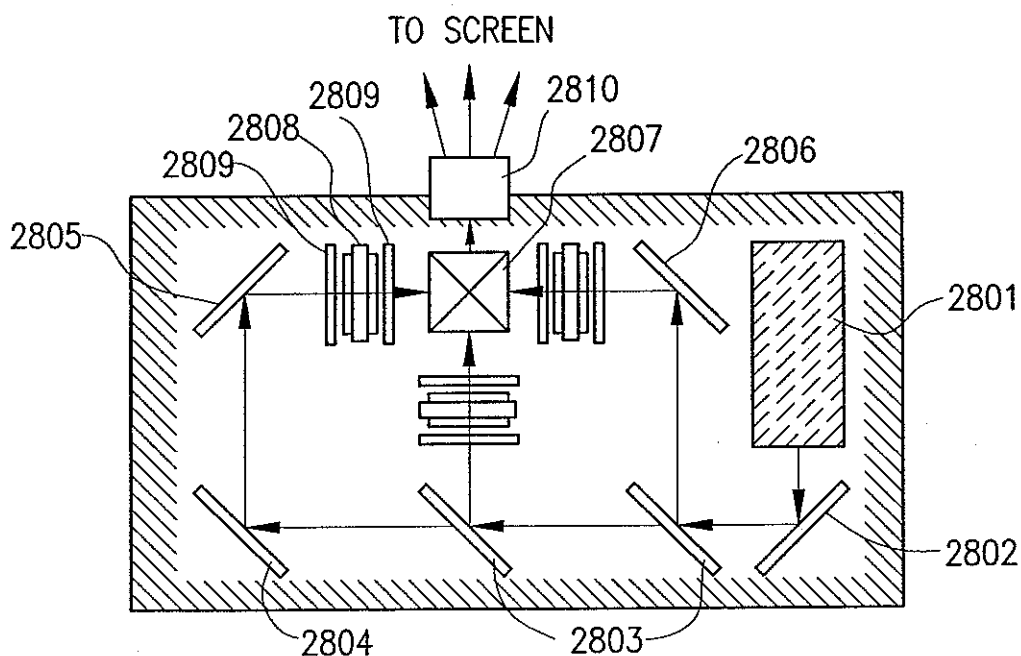
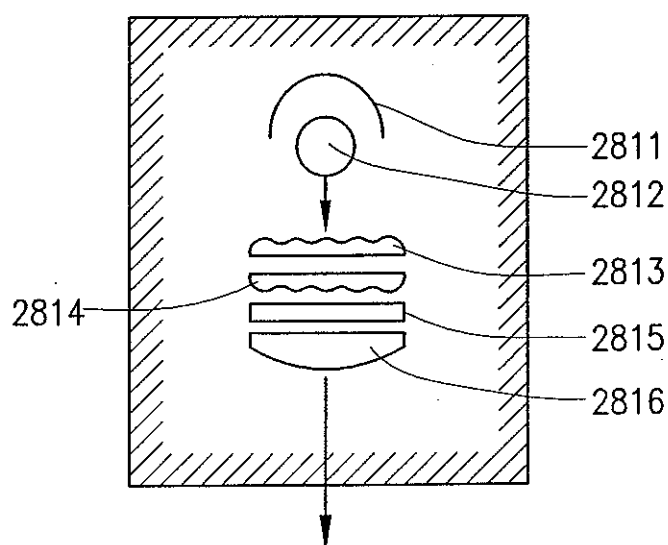


FIG. 11(D) OPTICAL LIGHT SOURCE SYSTEM



16/16

FIG. 12(A)

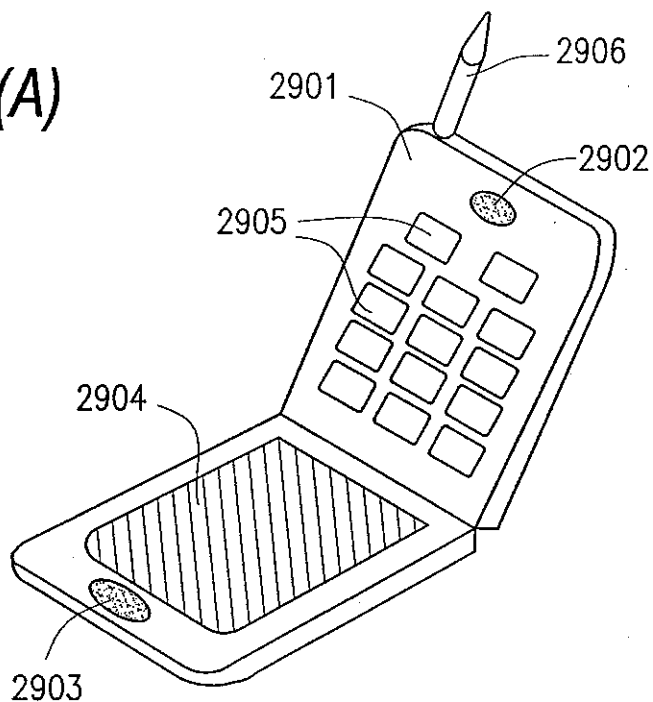


FIG. 12(B)

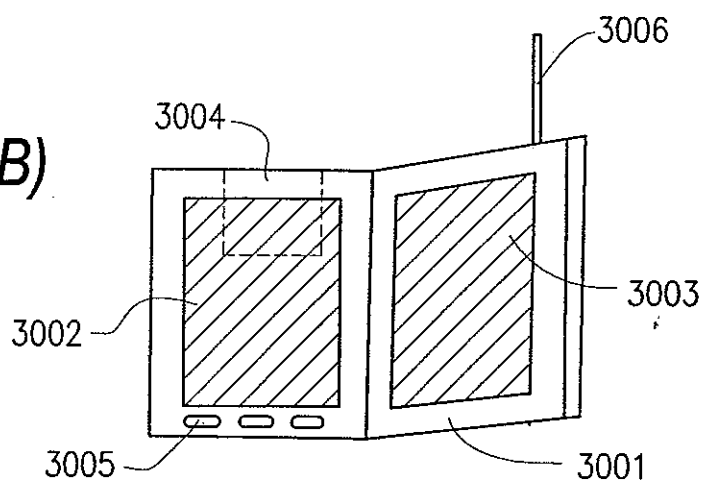


FIG. 12(C)

